

Silicon PNP Power Transistors

BDX88C

DESCRIPTION

- With TO-3 package
- Complement to type BDX87C
- DARLINGTON

APPLICATIONS

- Designed for use in power linear and switching application.

PINNING (See Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

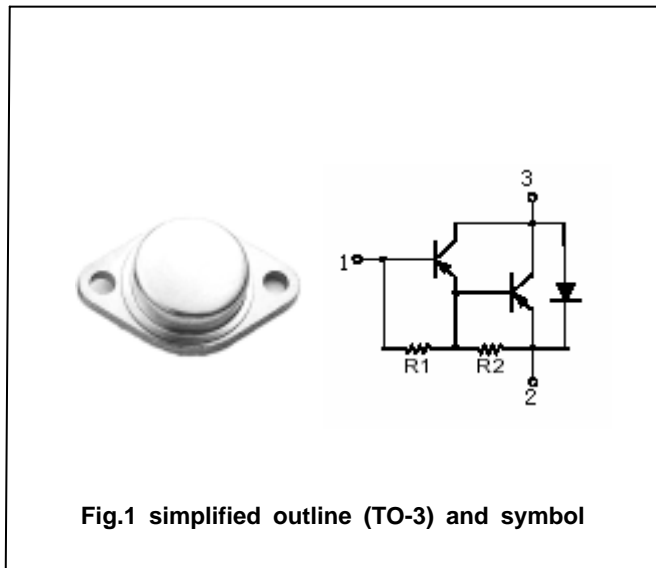


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-100	V
V _{CEO}	Collector-emitter voltage	Open base	-100	V
V _{EBO}	Emitter-base voltage	Open collector	-5	V
I _C	Collector current		-12	A
I _{CM}	Collector current(peak)		-18	A
I _B	Base current		-0.2	A
P _T	Total power dissipation	T _C =25	120	W
T _j	Max. operating Junction temperature		200	
T _{stg}	Storage temperature		-65~200	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal resistance from junction to case	1.45	/W

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CE0(SUS)}	Collector-emitter sustaining voltage	I _C =-0.1A ; I _B =0	-100			V
V _{CEsat-1}	Collector-emitter saturation voltage	I _C =-6A ; I _B =-24mA			-2.0	V
V _{CEsat-2}	Collector-emitter saturation voltage	I _C =-12A ; I _B =-120mA			-3.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =-12A ; I _B =-120mA			-4.0	V
V _{BE}	Base-emitter on voltage	I _C =-6A ; V _{CE} =-3V			-2.8	V
h _{FE-1}	DC current gain	I _C =-5A ; V _{CE} =-3V	1000			
h _{FE-2}	DC current gain	I _C =-6A ; V _{CE} =-3V	750		18000	
h _{FE-3}	DC current gain	I _C =-12A ; V _{CE} =-3V	100			
I _{CBO}	Collector cut-off current	V _{CB} =-100V ; I _E =0 T _C =150			-0.5 -5.0	mA
I _{CEO}	Collector cut-off current	V _{CE} =-50V ; I _B =0			-1.0	mA
I _{EBO}	Emitter cut-off current	V _{EB} =-5V ; I _C =0			-1.0	mA
V _{F-1}	Diode forward voltage	I _F =-3A			-1.8	V
V _{F-2}	Diode forward voltage	I _F =-8A		-2.5		V

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PACKAGE OUTLINE

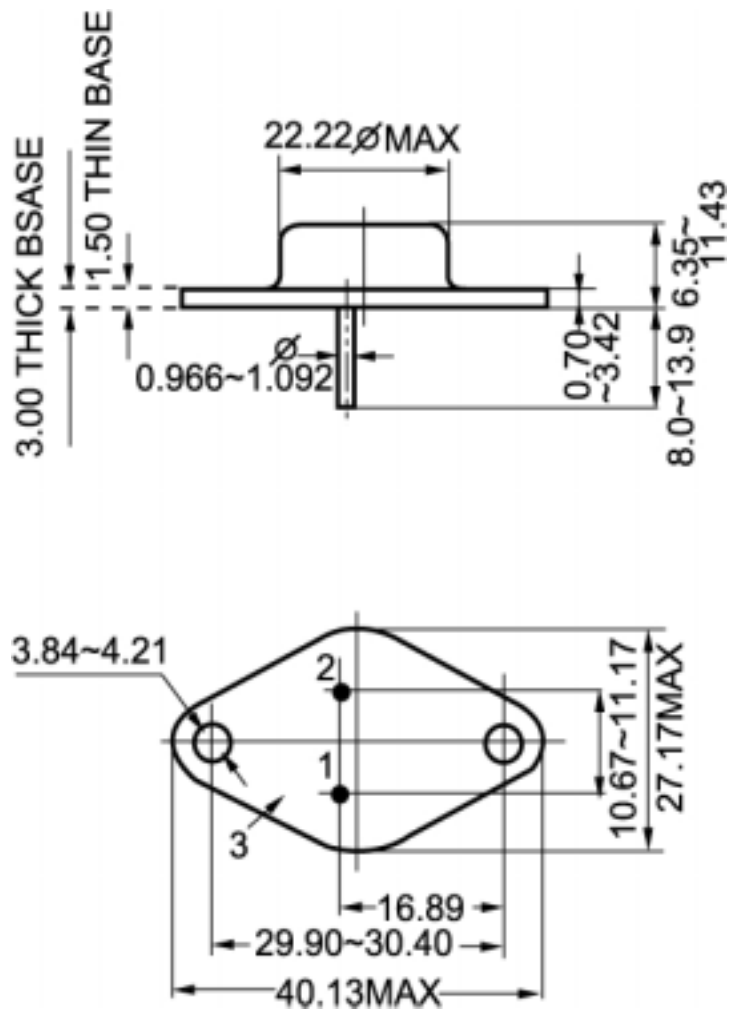


Fig.2 Outline dimensions